P54/74FCT821AT/BT/CT–
P54/74FCT823AT/BT/CT–P54/74FCT825AT/BT/CT
BUS INTERFACE REGISTERS

FEATURES

- **Function, Pinout and Drive Compatible with the FCT, F and Am29821/23/25 Logic**
- **FCT-C speed at 6.0ns max. (Com'l)**
  FCT-B speed at 7.5ns max. (Com'l)
- **Reduced V$_{OH}$ (typically = 3.3V) versions of Equivalent FCT functions**
- **Edge-rate Control Circuitry for Significantly Improved Noise Characteristics**
- **ESD protection exceeds 2000V**
- **Power-off disable feature**

- **Matched Rise and Fall times**
- **Fully Compatible with TTL Input and Output Logic Levels**
- **64 mA Sink Current (Com'l), 32 mA (Mil)**
  15 mA Source Current (Com'l), 12 mA (Mil)
- **High-Speed Parallel Registers with positive edge-triggered D-type Flip-Flops**
- **Buffered Common Clock Enable ($\overline{EN}$) and Asynchronous Clear Input ($\overline{CLR}$)**
- **Manufactured in 0.7 micron PACE Technology™**

DESCRIPTION

The 'FCT820T series bus interface registers are designed to eliminate the extra packages required to buffer existing registers and provide extra data width for wider address/data paths or buses carrying parity. The 'FCT821T is a buffered, 10 bit wide version of the popular 'FCT374 function. The 'FCT823T is a 9-bit wide buffered register with Clock Enable ($\overline{EN}$) and Clear ($\overline{CLR}$) — ideal for parity bus interfacing in high-performance microprogrammed systems. The 'FCT825T is a 8-bit buffered register with all the 'FCT823T controls plus multiple enables ($\overline{OE}_1$, $\overline{OE}_2$, $\overline{OE}_3$) to allow multiuser control of the interface, e.g., $\overline{CS}$, DMA and RD/$\overline{WR}$. They are ideal for use as an output port requiring high I$_{OL}$/I$_{OH}$.
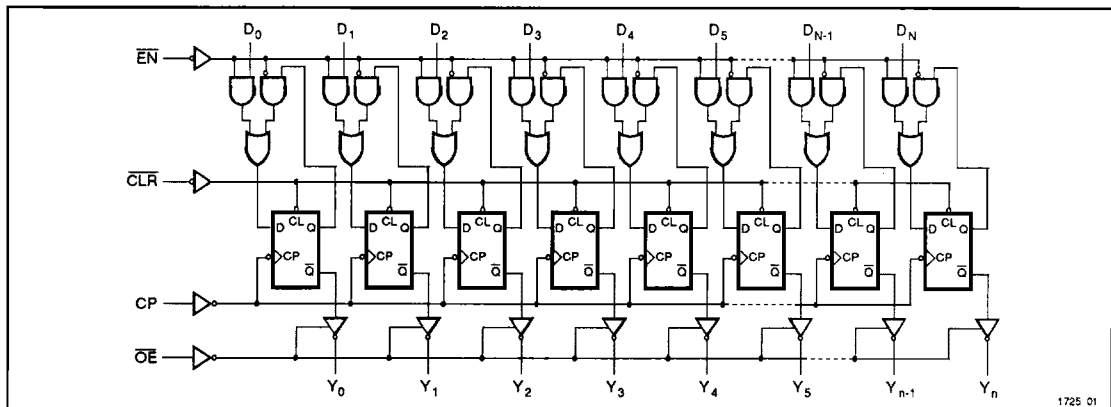
The 'FCT800T family of devices are designed for high-capacitance load drive capability, while providing low-

capacitance bus loading at both inputs and outputs. All inputs have clamp diodes and all outputs are designed for low-capacitance bus loading in the high impedance state.

The 'FCT820T interface family is manufactured using PACE Technology which is Performance Advanced CMOS Engineered to use 0.7 micron effective channel lengths giving 400 picoseconds loaded* internal gate delays. PACE Technology includes two-level metal and epitaxial substrates. In addition to very high performance and very high density, the technology features latch-up protection, single event upset protection, and is supported by a Class 1 environment volume production facility.

* For a fan-in/fan-out of 4, at 85°C junction temperature and 5.0V supply. For a fan-in/fan-out of 1, the internal gate delay is 200 picosecond at room temperature and 5.0V.

7

FUNCTIONAL BLOCK DIAGRAM

1725 01

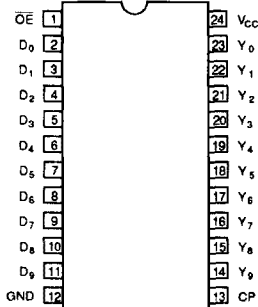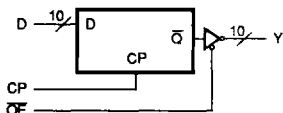2/13/92 - 4

PRODUCT SELECTOR GUIDE

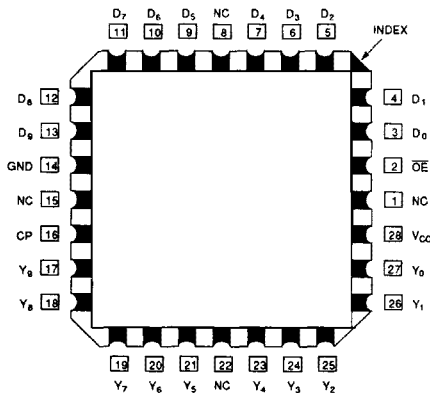| Non-inverting	Device		
	10-Bit	**9-Bit**	**8-Bit**
	'FCT821T	'FCT823T	'FCT825T

1725 Tbl 01

LOGIC SYMBOLS   PIN CONFIGURATONS

'FCT821T (10-Bit Register)
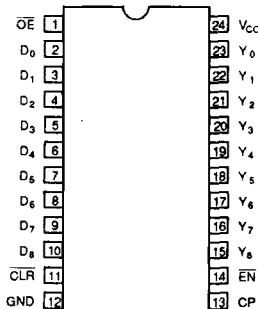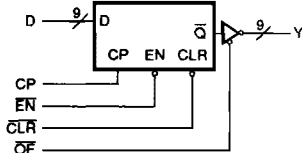

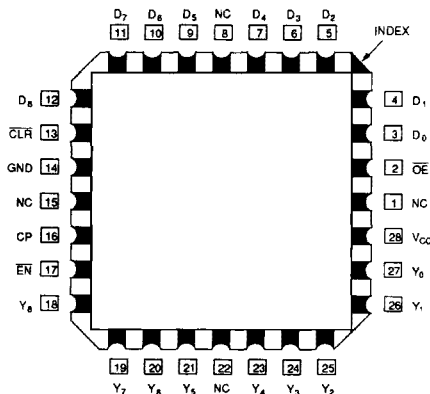DIP (D4,P4) SOIC (S4)   LCC (L5-1)   1725 02

'FCT823T (9-Bit Register)
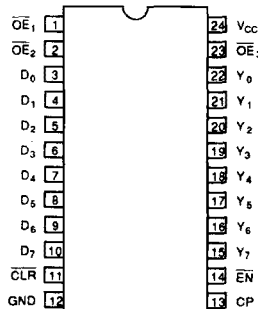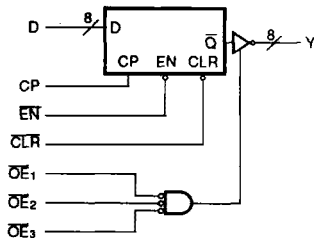

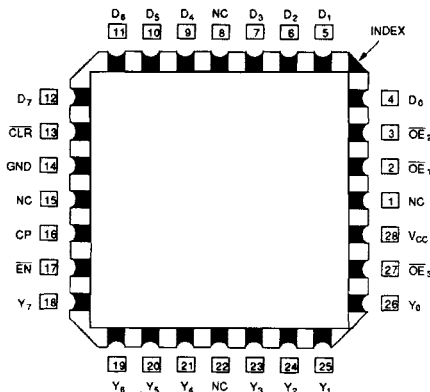DIP (D4,P4) SOIC (S4)   LCC (L5-1)   1725 03

'FCT825T (8-Bit Register)

DIP (D4,P4) SOIC (S4)   LCC (L5-1)   1725 04

ABSOLUTE MAXIMUM RATINGS[1,2]

Symbol	Parameter	Value	Unit
T_{STG}	Storage Temperature	−65 to +150	°C
T_A	Ambient Temperature Under Bias	−65 to +135	°C
V_{CC}	V_{CC} Potential to Ground	−0.5 to +7.0	V
P_T	Power Dissipation	0.5	W

1725 Tbl 02

Symbol	Parameter	Value	Unit
I_{OUTPUT}	Current Applied to Output	120	mA
V_{IN}	Input Voltage	−0.5 to +7.0	V
V_{OUT}	Voltage Applied to Output	−0.5 to +7.0	V

1725 Tbl 03

Notes:
1. Operation beyond the limits set forth in the above table may impair the useful life of the device. Unless otherwise noted, these limits are over the operating free-air temperature range.

2. Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.

RECOMMENDED OPERATING CONDITIONS

Free Air Ambient Temperature	Min	Max
Military	−55°C	+125°C
Commercial	0°C	+70°C

1725 Tbl 04

Supply Voltage (V_{CC})	Min	Max
Military	+4.5V	+5.5V
Commercial	+4.75V	+5.25V

1725 Tbl 05

DC ELECTRICAL CHARACTERISTICS (Over recommended operating conditions)

Symbol	Parameter		Min	Typ[1]	Max	Units	V_{CC}	Conditions
V_{IH}	Input HIGH Voltage		2.0			V		
V_{IL}	Input LOW Voltage				0.8	V		
V_H	Hysteresis			0.2		V		All inputs
V_{IK}	Input Clamp Diode Voltage			−0.7	−1.2	V	MIN	$I_{IN} = -18mA$
V_{OH}	Output HIGH Voltage	Military	2.4	3.3		V	MIN	$I_{OH} = -12mA$
		Commercial	2.4	3.3		V	MIN	$I_{OH} = -15mA$
V_{OL}	Output LOW Voltage	Military		0.3	0.5	V	MIN	$I_{OL} = 32mA$
		Commercial		0.3	0.5	V	MIN	$I_{OL} = 48mA$
		Commercial		0.3	0.5	V	MIN	$I_{OL} = 64mA$
I_I	Input HIGH Current				20	µA	MAX	$V_{IN} = V_{CC}$
I_{IH}	Input HIGH Current				5	µA	MAX	$V_{IN} = 2.7V$
I_{IL}	Input LOW Current				−5	µA	MAX	$V_{IN} = 0.5V$
I_{OZH}	Off State I_{OUT} HIGH-Level Output Current				10	µA	MAX	$V_{OUT} = 2.7V$
I_{OZL}	Off State I_{OUT} LOW-Level Output Current				−10	µA	MAX	$V_{OUT} = 0.5V$
I_{OS}	Output Short Circuit Current[2]		−60	−120	−225	mA	MAX	$V_{OUT} = 0.0V$
I_{OFF}	Power-off Disable				100	µA	0V	$V_{OUT} = 4.5V$
C_{IN}	Input Capacitance[3]			6	10	pF	MAX	All inputs
C_{OUT}	Output Capacitance[3]			8	12	pF	MAX	All outputs
I_{CC}	Quiescent Power Supply Current			0.2	1.5	mA	MAX	$V_{IN} \leq 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$

1725 Tbl 05

Notes:
1. Typical limits are at $V_{CC} = 5.0V$, $T_A = +25°C$ ambient.
2. Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parameter tests. In any sequence of parameter tests, I_{os} tests should be performed last.
3. This parameter is guaranteed but not tested.

7

2/13/92 - 4

DC CHARACTERISTICS (Over recommended operating conditions unless otherwise specified.)

Symbol	Parameter	Typ[1]	Max	Units	Conditions
ΔI_{CC}	Quiescent Power Supply Current (TTL inputs)	0.5	2.0	mA	V_{CC} = MAX, V_{IN} = 3.4V[2], f_i = 0, Outputs Open
I_{CCD}	Dynamic Power Supply Current[3]	0.15	0.25	mA/ mHz	V_{CC} = MAX, One Bit Toggling, 50% Duty Cycle, Outputs Open, $\overline{OE}$ = $\overline{EN}$ = GND, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$
I_C	Total Power Supply Current[5]	1.7	4.0	mA	V_{CC} = MAX, f_0 = 10MHz, 50% Duty Cycle, Outputs Open, One Bit Toggling at f_i = 5MHz, $\overline{OE}$ = $\overline{EN}$ = GND, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$
		2.2	6.0	mA	V_{CC} = MAX, f_0 = 10MHz, 50% Duty Cycle, Outputs Open, One Bit Toggling at f_i = 5MHz, $\overline{OE}$ = $\overline{EN}$ = GND, V_{IN} = 3.4V or V_{IN} = GND
		4.0	7.8[4]	mA	V_{CC} = MAX, f_0 = 10MHz, 50% Duty Cycle, Outputs Open, Eight Bits Toggling at f_i = 2.5MHz, $\overline{OE}$ = $\overline{EN}$ = GND, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$
		6.2	16.8[4]	mA	V_{CC} = MAX, f_0 = 10MHz, 50% Duty Cycle, Outputs Open, Eight Bits Toggling at f_i = 2.5MHz, $\overline{OE}$ = $\overline{EN}$ = GND, V_{IN} = 3.4V or V_{IN} = GND

1725 Tbl 07

Notes:
1. Typical values are at V_{CC} = 5.0V, +25°C ambient.
2. Per TTL driven input (V_{IN} = 3.4V); all other inputs at V_{CC} or GND.
3. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
4. Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.
5. I_C = $I_{QUIESCENT}$ + I_{INPUTS} + $I_{DYNAMIC}$
   I_C = I_{CC} + $\Delta I_{CC} D_H N_T$ + $I_{CCD}(f_0/2 + f_i N_i)$
   I_{CC} = Quiescent Current with CMOS input levels
   ΔI_{CC} = Power Supply Current for a TTL High Input (V_{IN} = 3.4V)

D_H = Duty Cycle for TTL Inputs High
N_T = Number of TTL Inputs at D_H
I_{CCD} = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)
f_0 = Clock Frequency for Register Devices (Zero for Non-Register Devices)
f_i = Input Frequency
N_i = Number of Inputs at f_i
All currents are in milliamps and all frequencies are in megahertz.

AC CHARACTERISTICS

Sym.	Parameter	Test Conditions	'FCT821AT–825AT				'FCT821BT–825BT				'FCT821CT–825CT				Units	Fig. No.
			MIL		COM'L		MIL		COM'L		MIL		COM'L			
			Min.[1]	Max.	Min.[1]	Max.	Min.[1]	Max.	Min.[1]	Max.	Min.[1]	Max.	Min.[1]	Max		
t_{PLH} t_{PHL}	Propagation Delay CP to Y_1 ($\overline{OE}$ = LOW)	C_L = 50pF R_L = 500Ω	–	11.5	–	10.0	–	8.5	–	7.5	–	7.0	–	6.0	ns	1,5
t_{PLH} t_{PHL}	Propagation Delay CP to Y_1 ($\overline{OE}$ = LOW)	C_L = 300pF[2] R_L = 500Ω	–	20.0	–	20.0	–	16.0	–	15.0	–	13.5	–	12.5	ns	1,5
t_{PLH}	Propagation Delay $\overline{CLR}$ to Y_1	C_L = 50pF R_L = 500Ω	–	15.0	–	14.0	–	9.5	–	9.0	–	8.5	–	8.0	ns	1,5
t_{PZH} t_{PZL}	Output Enable Time $\overline{OE}$ to Y_1	C_L = 50pF R_L = 500Ω	–	13.0	–	12.0	–	9.0	–	8.0	–	8.0	–	7.0	ns	1,7,8
t_{PZH} t_{PZL}	Output Enable Time $\overline{OE}$ to Y_1	C_L = 300pF[2] R_L = 500Ω	–	25.0	–	23.0	–	16.0	–	15.0	–	13.5	–	12.5	ns	1,7,8
t_{PHZ} t_{PHL}	Output Disable Time $\overline{OE}$ to Y_1	C_L = 5pF[2] R_L = 500Ω	–	8.0	–	7.0	–	7.0	–	6.5	–	6.2	–	6.2	ns	1,7,8
t_{PHZ} t_{PHL}	Output Disable Time $\overline{OE}$ to Y_1	C_L = 50pF R_L = 500Ω	–	9.0	–	8.0	–	8.0	–	7.5	–	6.5	–	6.5	ns	1,7,8

1725 Tbl 08

AC OPERATING REQUIREMENTS

Sym.	Parameter	Test Conditions	'FCT821AT–825AT				'FCT821BT–825BT				'FCT821CT–825CT				Units	Fig. No.
			MIL		COM'L		MIL		COM'L		MIL		COM'L			
			Min.[1]	Max.	Min.[1]	Max.	Min.[1]	Max.	Min.[1]	Max.	Min.[1]	Max.	Min.[1]	Max		
t_{SU}	Data to CP Set-up Time		4.0	–	4.0	–	3.0	–	3.0	–	3.0	–	3.0	–	ns	4
t_h	Data CP Hold Time		2.0	–	2.0	–	1.5	–	1.5	–	1.5	–	1.5	–	ns	4
t_{su}	Enable $\overline{EN}$ to CP Set-up Time		4.0	–	4.0	–	3.0	–	3.0	–	3.0	–	3.0	–	ns	9
t_h	Enable $\overline{EN}$ to CP Hold Time	C_L = 50pF R_L = 500Ω	2.0	–	2.0	–	0.0	–	0.0	–	0.0	–	0.0	–	ns	9
t_{REM}	Clear Recovery Time $\overline{CLR}$ to CP		7.0	–	6.0	–	6.0	–	6.0	–	6.0	–	6.0	–	ns	6
t_w	Clock Pulse Width		7.0	–	7.0	–	6.0	–	6.0	–	6.0		6.0	–	ns	5
t_w	$\overline{CLR}$ Pulse Width LOW		7.0	–	6.0	–	6.0	–	6.0	–	6.0		6.0	–	ns	5

1725 Tbl 09

Notes:
1. Minimum limits are guaranteed but not tested on Propagation Delays.
2. These parameters are guaranteed but not tested.

7

2/13/92 - 4

PIN DESCRIPTION

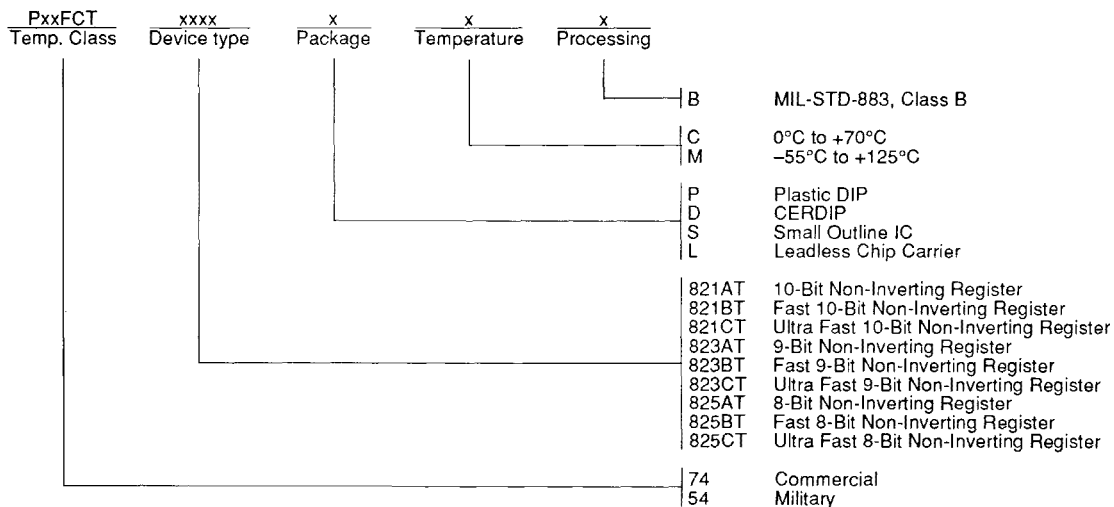| Name	I/O	Description
D_1	I	The D flip-flop data inputs.
$\overline{CLR}$	I	For both inverting and non-inverting registers, when the clear input is LOW and $\overline{OE}$ is LOW, the Q_1 outputs are LOW. When the clear input is HIGH, data can be entered into the register.
CP	O	Clock Pulse for the register; enters data into the register on the LOW-to-HIGH transition.
$Y_1, \overline{Y}_1$	O	The register three-state outputs.
$\overline{EN}$	I	Clock Enable. When the clock enable is LOW, data on the D_1 input is transferred to the Q_1 output on the LOW-to HIGH clock transition. When the clock enable is HIGH, the Q_1 outputs do not change state, regardless of the data or clock input transitions.
$\overline{OE}$	I	Output Control. When the $\overline{OE}$ input is HIGH, the Y_1 outputs are in the high impedence state. When the $\overline{OE}$ input is LOW, the TRUE register data is present at the Y_1 outputs.

1725 Tbl 10

FUNCTION TABLES

Inputs					Internal Outputs		Function
$\overline{OE}$	$\overline{CLR}$	$\overline{EN}$	D_1	CP	Q_1	Y_1	
H	H	L	L	Γ	L	Z	High Z
H	H	L	H	Γ	H	Z	
H	L	X	X	X	L	Z	Clear
L	L	X	X	X	L	L	
H	H	H	X	X	NC	Z	Hold
L	H	H	X	X	NC	NC	
H	H	L	L	Γ	L	Z	Load
H	H	L	H	Γ	H	Z	
L	H	L	L	Γ	L	L	
L	H	L	H	Γ	H	H	

1725 Tbl 11

H = HIGH, L = LOW, X = Don't Care, NC = No Change,
Γ = LOW-to-HIGH Transition, Z = HIGH Impedance

ORDERING INFORMATION

PxxFCT	xxxx	x	x	x
Temp. Class	Device type	Package	Temperature	Processing

B	MIL-STD-883, Class B
C	0°C to +70°C
M	−55°C to +125°C
P	Plastic DIP
D	CERDIP
S	Small Outline IC
L	Leadless Chip Carrier
821AT	10-Bit Non-Inverting Register
821BT	Fast 10-Bit Non-Inverting Register
821CT	Ultra Fast 10-Bit Non-Inverting Register
823AT	9-Bit Non-Inverting Register
823BT	Fast 9-Bit Non-Inverting Register
823CT	Ultra Fast 9-Bit Non-Inverting Register
825AT	8-Bit Non-Inverting Register
825BT	Fast 8-Bit Non-Inverting Register
825CT	Ultra Fast 8-Bit Non-Inverting Register
74	Commercial
54	Military

1725 05